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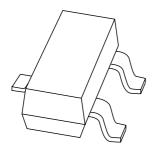
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Kind regards,

Team Nexperia

# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# PMBT3904 NPN switching transistor

Product data sheet Supersedes data of 1999 Apr 27 2004 Jan 12



# **NPN** switching transistor

### **PMBT3904**

#### **FEATURES**

- Collector current capability I<sub>C</sub> = 200 mA
- Collector-emitter voltage V<sub>CEO</sub> = 40 V.

#### **APPLICATIONS**

• General switching and amplification.

#### **DESCRIPTION**

NPN switching transistor in a SOT23 plastic package. PNP complement: PMBT3906.

#### **MARKING**

TYPE NUMBER	MARKING CODE(1)
PMBT3904	*1A

#### Note

1. \* = p: Made in Hong Kong.

\* = t : Made in Malaysia.

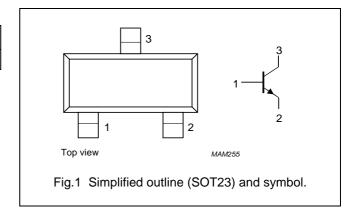
\* = W : Made in China.

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	40	٧
I <sub>C</sub>	collector current (DC)	200	mA

#### **PINNING**

PIN	DESCRIPTION
1	base
2	emitter
3	collector



#### **ORDERING INFORMATION**

TYPE		PACKAGE					
NUMBER	NAME	DESCRIPTION	VERSION				
PMBT3904	1	plastic surface mounted package; 3 leads	SOT23				

# NPN switching transistor

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#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	-	60	V
$V_{CEO}$	collector-emitter voltage	open base	-	40	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	6	V
I <sub>C</sub>	collector current (DC)		-	200	mA
I <sub>CM</sub>	peak collector current		-	200	mA
I <sub>BM</sub>	peak base current		-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	-	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

#### THERMAL CHARACTERISTICS

SYI	MBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-</sub>	a)	thermal resistance from junction to ambient	note 1	500	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 30 V	_	50	nA
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 6 V	_	50	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 1 V; see Fig.2; note 1			
		$I_{C} = 0.1 \text{ mA}$	60	_	
		$I_C = 1 \text{ mA}$	80	_	
		I <sub>C</sub> = 10 mA	100	300	
		I <sub>C</sub> = 50 mA	60	_	
		I <sub>C</sub> = 100 mA	30	_	
V <sub>CEsat</sub>	collector-emitter saturation	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA	_	200	mV
	voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	_	300	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA	650	850	mV
		I <sub>C</sub> = 50 mA; I <sub>B</sub> = 5 mA	-	950	mV
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = I <sub>e</sub> = 0; V <sub>CB</sub> = 5 V; f = 1 MHz	_	4	pF
C <sub>e</sub>	emitter capacitance	$I_C = I_c = 0$ ; $V_{BE} = 500 \text{ mV}$ ; $f = 1 \text{ MHz}$	_	8	pF

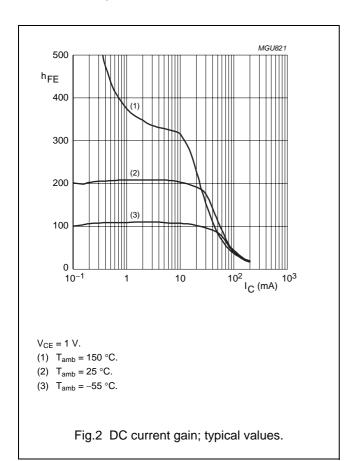
# NPN switching transistor

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SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
f <sub>T</sub>	transition frequency	$I_C = 10 \text{ mA}; V_{CE} = 20 \text{ V};$ f = 100 MHz	300	_	MHz
F	noise figure	$I_C = 100 \ \mu A; \ V_{CE} = 5 \ V; \ R_S = 1 \ k\Omega;$ f = 10 Hz to 15.7 kHz	-	5	dB
Switching ti	imes (between 10% and 90% lev	els); see Fig.3			
t <sub>d</sub>	delay time	I <sub>Con</sub> = 10 mA; I <sub>Bon</sub> = 1 mA;	_	35	ns
t <sub>r</sub>	rise time	$I_{Boff} = -1 \text{ mA}$	_	35	ns
t <sub>s</sub>	storage time		_	200	ns
t <sub>f</sub>	fall time		_	50	ns

#### Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 



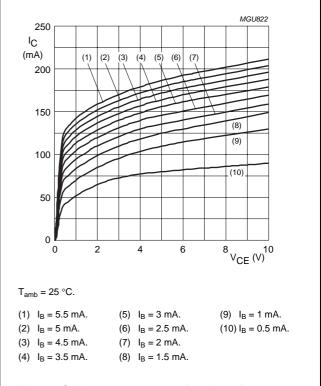
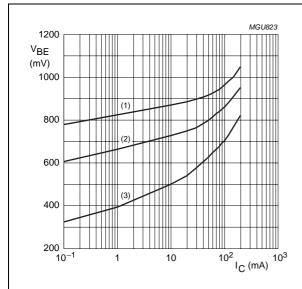


Fig.3 Collector current as a function of collector-emitter voltage.

# NPN switching transistor

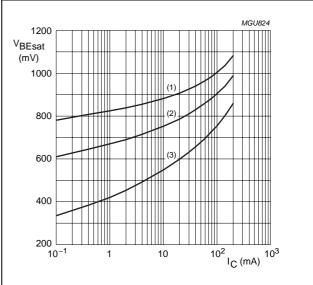
# PMBT3904



 $V_{CE} = 1 V$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

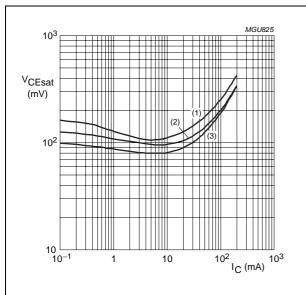
Fig.4 Base-emitter voltage as a function of collector current.



 $I_{\rm C}/I_{\rm B} = 10.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.5 Base-emitter saturation voltage as a function of collector current.



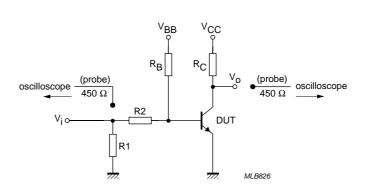
 $I_{\rm C}/I_{\rm B}=10.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.6 Collector-emitter saturation voltage as a function of collector current.

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 $V_i$  = 5 V; T = 500  $\mu s;$   $t_p$  = 10  $\mu s;$   $t_r$  =  $t_f \leq 3$  ns.

R1 = 56  $\Omega$ ; R2 = 2.5 k $\Omega$ ; R<sub>B</sub> = 3.9 k $\Omega$ ; R<sub>C</sub> = 270  $\Omega$ .

 $V_{BB} = -1.9 \text{ V}$ ;  $V_{CC} = 3 \text{ V}$ .

Oscilloscope: input impedance  $Z_i$  = 50  $\Omega$ .

Fig.7 Test circuit for switching times.

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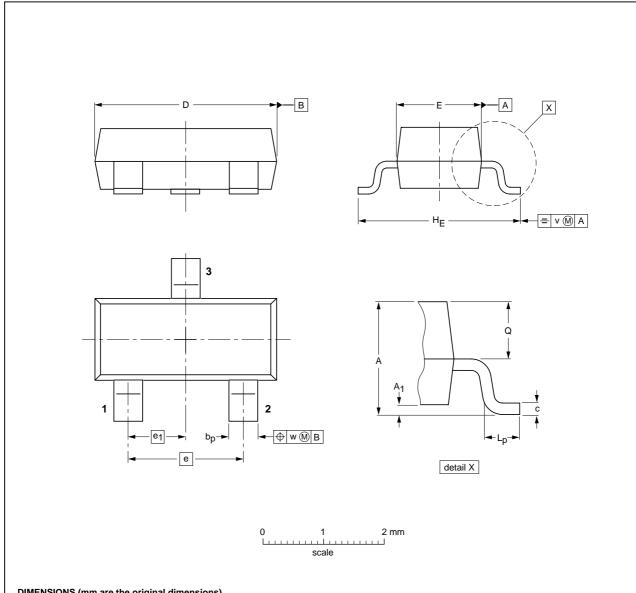
# NPN switching transistor

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#### **PACKAGE OUTLINE**



SOT23



#### **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	A <sub>1</sub> max.	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFERENCES EUROPEAN 1981 F. P.					
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT23		TO-236AB				<del>-04-11-04</del> 06-03-16	

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## NPN switching transistor

**PMBT3904** 

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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